

N-channel 600 V, 7 A - IPAK Very fast PowerMESH™ IGBT

Datasheet - production data

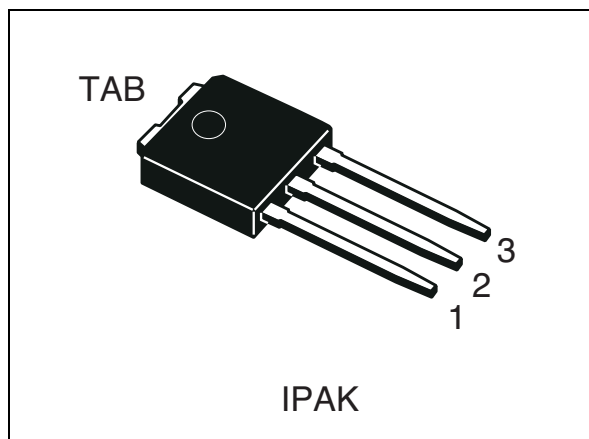
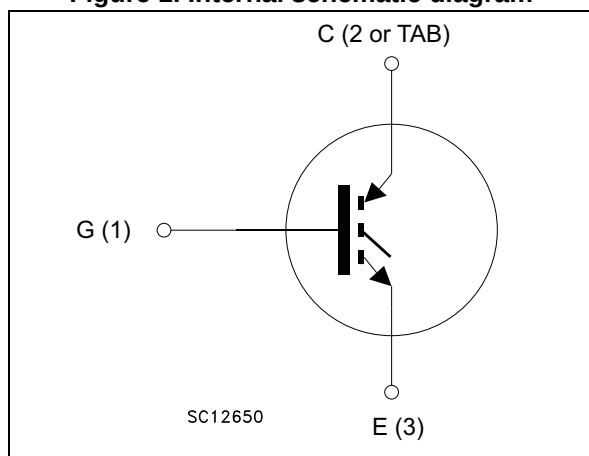


Figure 1. Internal schematic diagram



Features

Type	V_{CES}	$V_{CE(sat)}$ max@25°C	I_C @100°C
STGD6NC60H	600V	<2.5V	7A

- Low on voltage drop (V_{cesat})
- Low C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- High frequency operation

Description

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix H identifies a family optimized for high frequency application in order to achieve very high switching performances (reduced t_{fall}) maintaining a low voltage drop.

Applications

- High frequency inverters
- SMPS and PFC in both hard switch and resonant topologies
- Motor drivers

Table 1. Device summary

Part number	Marking	Package	Packaging
STGD6NC60H-1	GD6NC60H	IPAK	Tube

Contents

1 **Electrical ratings** **3**

2 **Electrical characteristics** **4**

 2.1 Electrical characteristics (curves) 6

3 **Test circuit** **9**

4 **Package mechanical data** **10**

5 **Revision history** **12**



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GS} = 0$)	600	V
$I_C^{(1)}$	Collector current (continuous) at $T_C = 25^\circ\text{C}$	15	A
$I_C^{(1)}$	Collector current (continuous) at $T_C = 100^\circ\text{C}$	7	A
$I_{CM}^{(2)}$	Collector current (pulsed)	21	A
V_{GE}	Gate-emitter voltage	± 20	V
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	62.5	W
T_{stg}	Storage temperature	– 55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature		
T_l	Maximum lead temperature for soldering purpose (for 10sec. 1.6 mm from case)	300	$^\circ\text{C}$

1. Calculated according to the iterative formula.:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2. Pulse width limited by max junction temperature

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	100	$^\circ\text{C/W}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-emitter breakdown voltage	$I_C = 1\text{mA}$, $V_{GE} = 0$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}$, $I_C = 3\text{A}$ $V_{GE} = 15\text{V}$, $I_C = 3\text{A}$, $T_C = 125^{\circ}\text{C}$		1.9 1.7	2.5	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.75		5.75	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{V}$ $V_{CE} = 600\text{V}$, $T_C = 125^{\circ}\text{C}$			10 1	μA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$			± 100	nA
g_{fs}	Forward transconductance	$V_{CE} = 15\text{V}$, $I_C = 3\text{A}$		3		S

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{V}$, $f = 1\text{MHz}$, $V_{GE} = 0$	-	205	-	pF
C_{oes}	Output capacitance		-	32	-	pF
C_{res}	Reverse transfer capacitance		-	5.5	-	pF
Q_g	Total gate charge	$V_{CE} = 390\text{V}$, $I_C = 3\text{A}$, $V_{GE} = 15\text{V}$, (see Figure 17)	-	13.6	-	nC
Q_{ge}	Gate-emitter charge			3.4		nC
Q_{gc}	Gate-collector charge			5.1		nC
I_{CL}	Turn-off SOA minimum current	$V_{clamp} = 390\text{V}$, $T_j = 150^{\circ}\text{C}$, $R_G = 10\Omega$, $V_{GE} = 15\text{V}$	-	19	-	A

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V,$ (see Figure 18)	-	12	-	ns
t_r	Current rise time		-	5	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	612	-	A/ μs
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V,$ $T_j = 125^\circ C$ (see Figure 18)	-	13	-	ns
t_r	Current rise time		-	4.3	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	560	-	A/ μs
$t_{r(voff)}$	Off voltage rise time	$V_{CC} = 390V, I_C = 3A,$ $R_{GE} = 10\Omega, V_{GE} = 15V$ (see Figure 18)	-	40	-	ns
$t_{d(off)}$	Turn-off delay time		-	76	-	ns
t_f	Current fall time		-	100	-	ns
$t_{r(voff)}$	Off voltage rise time	$V_{CC} = 390V, I_C = 3A,$ $R_{GE} = 10\Omega, V_{GE} = 15V,$ $T_j = 125^\circ C$ (see Figure 18)	-	60	-	ns
$t_{d(off)}$	Turn-off delay time		-	98	-	ns
t_f	Current fall time		-	124	-	ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V$ (see Figure 18)	-	20	-	μJ
$E_{off}^{(2)}$	Turn-off switching losses		-	68	-	μJ
E_{ts}	Total switching losses		-	88	-	μJ
$E_{on}^{(1)}$	Turn-on switching losses	$V_{CC} = 390V, I_C = 3A$ $R_G = 10\Omega, V_{GE} = 15V, T_j = 125^\circ C$ (see Figure 18)	-	37	-	μJ
$E_{off}^{(2)}$	Turn-off switching losses		-	93	-	μJ
E_{ts}	Total switching losses		-	130	-	μJ

1. E_{on} is the turn-on losses when a typical diode is used in the test circuit in Figure 18. If the IGBT is offered in a package with a co-pak diode, the co-pak diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

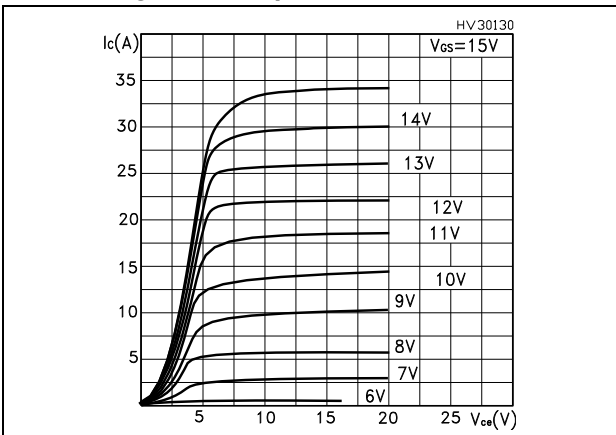


Figure 3. Transfer characteristics

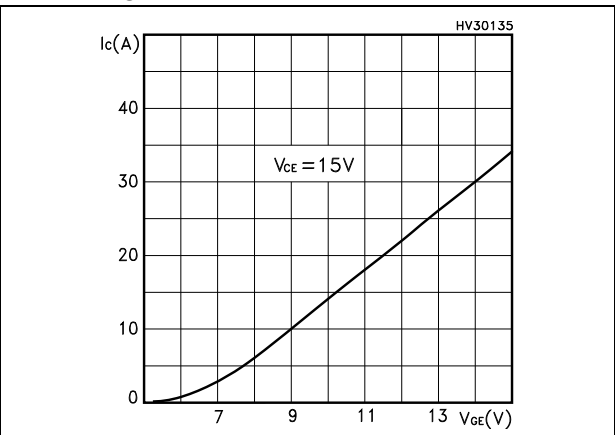


Figure 4. Transconductance

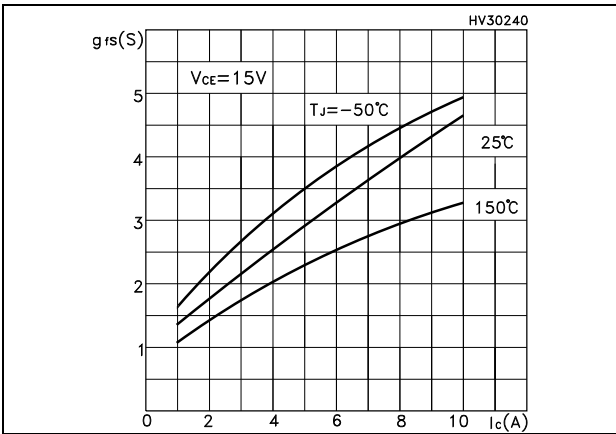


Figure 5. Collector-emitter on voltage vs temperature

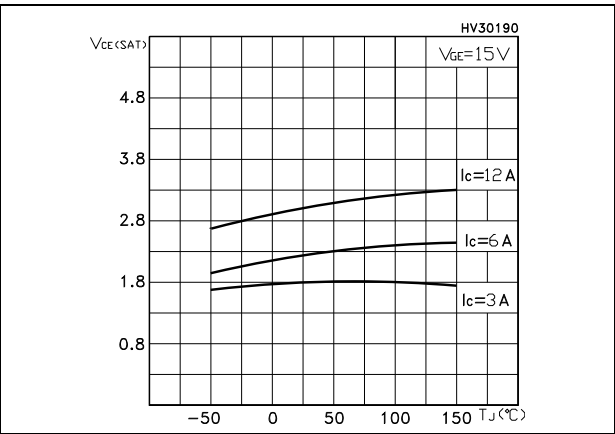


Figure 6. Gate charge vs gate-source voltage

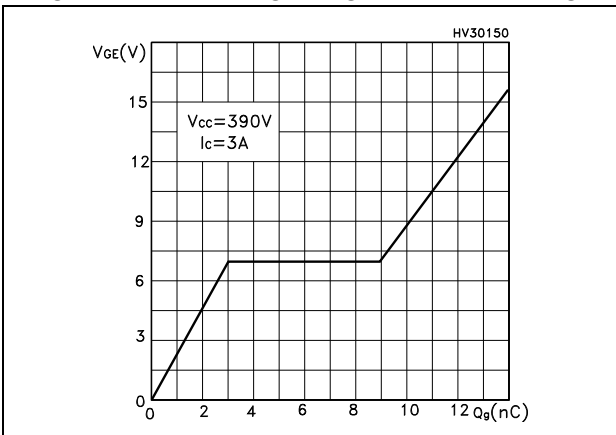


Figure 7. Capacitance variations

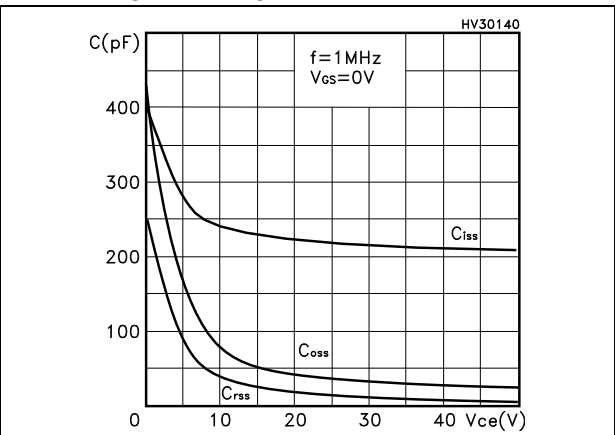


Figure 8. Normalized gate threshold voltage vs temperature

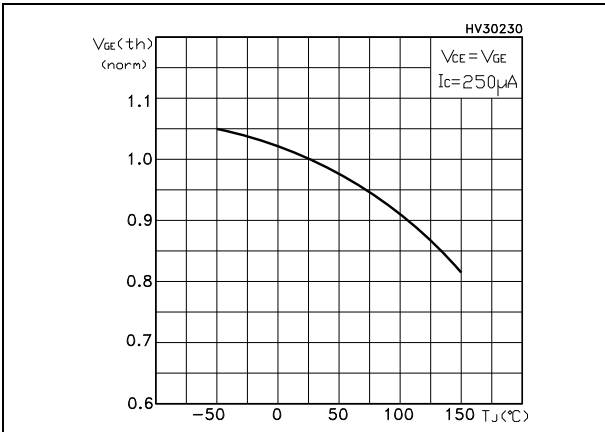


Figure 9. Collector-emitter on voltage vs collector current

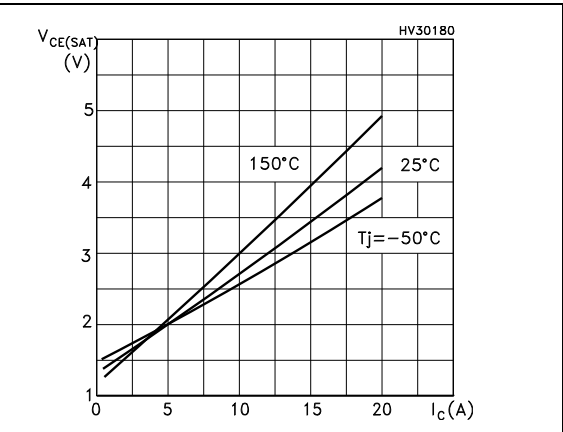


Figure 10. Normalized breakdown voltage vs temperature

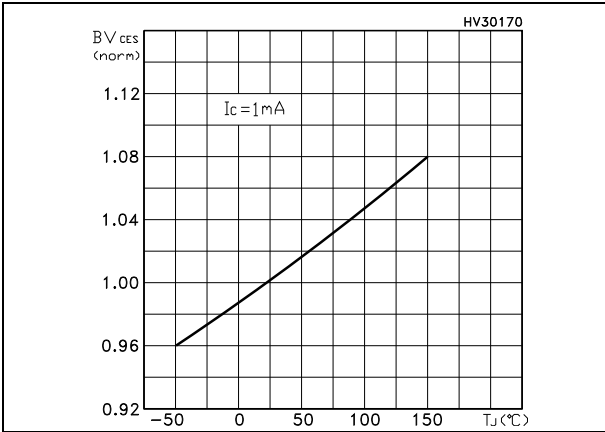


Figure 11. Switching losses vs temperature

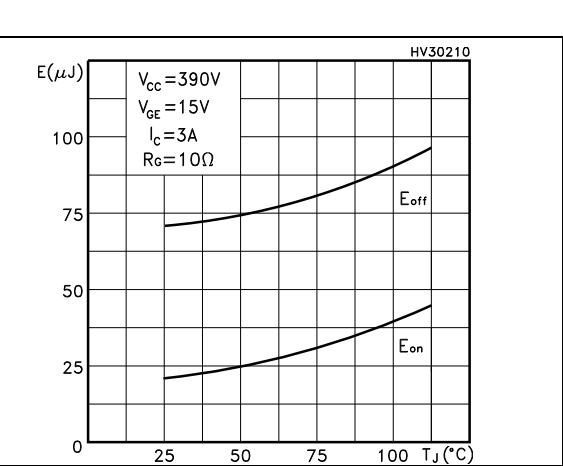


Figure 12. Switching losses vs gate resistance

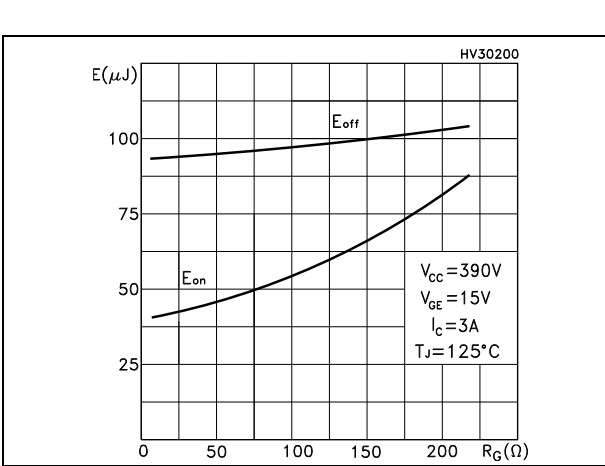


Figure 13. Switching losses vs collector current

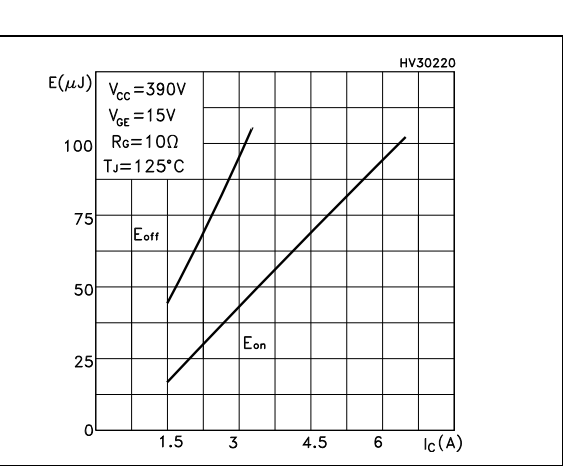


Figure 14. Thermal impedance

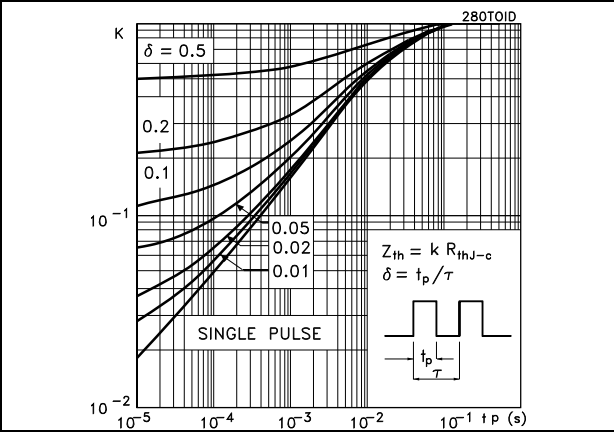


Figure 15. Turn-off SOA

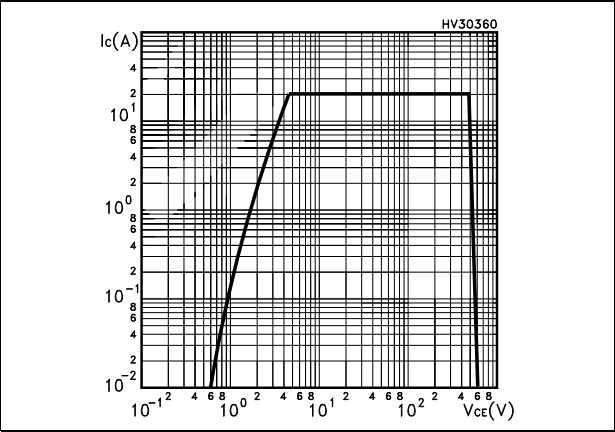
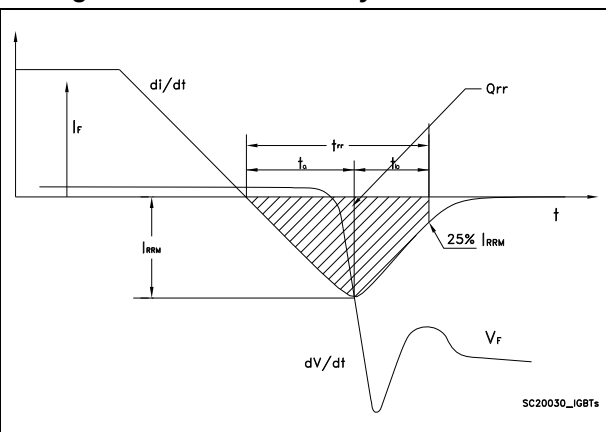
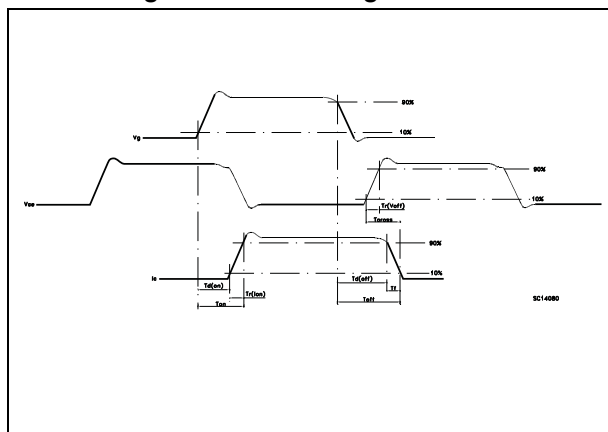
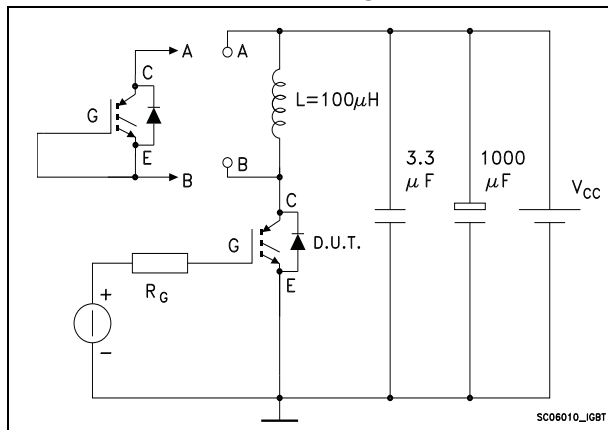


Figure 16. Test circuit for inductive load switching



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 20. IPAK (TO-251) drawing

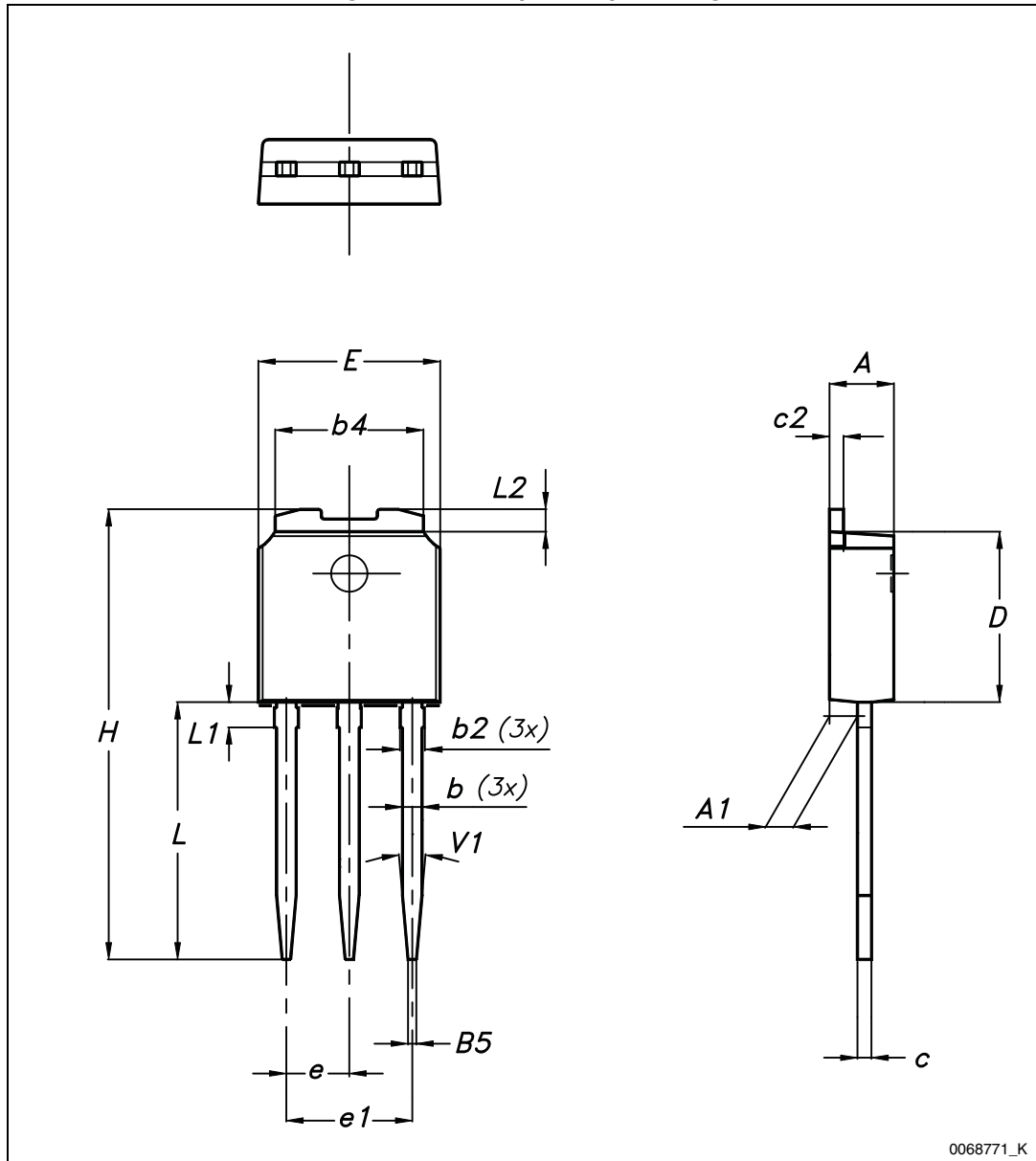


Table 8. IPAK (TO-251) mechanical data

DIM	mm.		
	min.	typ.	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

5 Revision history

Table 9. Revision history

Date	Revision	Changes
08-Apr-2014	1	First release.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2014 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[STMicroelectronics:](#)

[STGD6NC60H-1](#)